



(19)

(11) Publication number:

03185817 A

Generated Document.

## PATENT ABSTRACTS OF JAPAN

(21) Application number: 01325034

(51) Intl. Cl.: H01L 21/205 H01L 21/263

(22) Application date: 15.12.89

(30) Priority:

(43) Date of application  
publication: 13.08.91(84) Designated contracting  
states:

(71) Applicant: SEIKO EPSON CORP

(72) Inventor: IWAMATSU SEIICHI

(74) Representative:

(54) METHOD OF FORMING  
SEMICONDUCTOR FILM

(57) Abstract:

**PURPOSE:** To enable polycrystalline Si film growth and epitaxial growth of large mobility at a low temperature, by forming an Si film on a substrate by using thermal decomposition or optical decomposition of specified silane material.

**CONSTITUTION:** An Si film is formed on a substrate by thermally or optically decomposing raw material of

silane ( $\text{SiH}_2\text{n}+2$ ), n = 3, like trisilane ( $\text{Si}_3\text{H}_8$ ) and tetrasilane ( $\text{Si}_4\text{H}_{10}$ ). By CVD method, a polycrystalline Si film whose grain diameter is about  $3\mu\text{m}$  can be formed when the temperature of a Pyrex glass substrate is  $400^\circ\text{C}$ . A TFT using an Si film has large electric charge mobility and high speed operation is realized. The similar polycrystal can be obtained by irradiating the surface of the substrate at  $100^\circ\text{C}$  with ultraviolet rays. In order to epitaxially grow a single crystal Si film on a single crystal Si substrate by using  $\text{Si}_3\text{H}_8$  or  $\text{Si}_4\text{H}_{10}$  as raw material, the substrate temperature is set at  $100^\circ\text{C}$ , and ultraviolet rays are projected or plasma is utilized.

COPYRIGHT: (C)1991,JPO&Japio